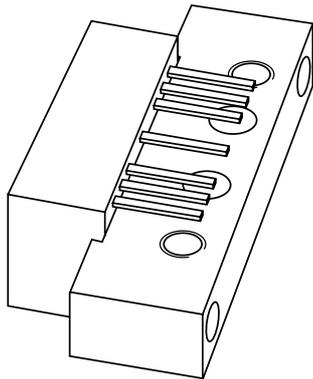


# DATA SHEET



## **BGR269** 200 MHz, 35 dB gain reverse amplifier

Product specification  
Supersedes data of 2001 Oct 03

2002 Mar 05

# 200 MHz, 35 dB gain reverse amplifier

# BGR269

### FEATURES

- Excellent linearity
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability
- 35 dB amplification up to 200 MHz.

### APPLICATIONS

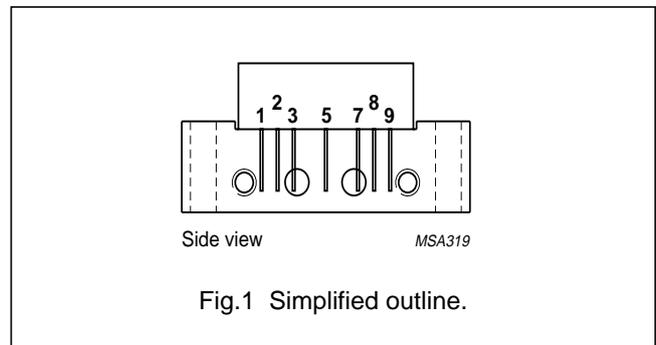
- Reverse amplifier in two-way CATV systems operating in the 5 to 200 MHz frequency range.

### DESCRIPTION

High performance amplifier in a SOT115J package, operating at a voltage supply of 24 V (DC).

### PINNING - SOT115J

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V <sub>B</sub>
7	common
8	common
9	output



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 5 MHz	34.5	35	35.5	dB
		f = 200 MHz	35	–	36	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	145	160	175	mA

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V <sub>i</sub>	RF input voltage	–	50	dBmV
T <sub>mb</sub>	operating mounting base temperature	–20	+100	°C
T <sub>stg</sub>	storage temperature range	–40	+100	°C

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**CHARACTERISTICS**Bandwidth 5 to 200 MHz;  $V_B = 24\text{ V}$ ;  $T_{mb} = 30\text{ °C}$ ;  $Z_S = Z_L = 75\ \Omega$ .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$G_p$	power gain	f = 5 MHz	34.5	35	35.5	dB
		f = 200 MHz	35	–	36	dB
SL	slope straight line	f = 5 to 200 MHz	0	–	0.6	dB
FL	flatness of frequency response	f = 5 to 10 MHz	–0.1	–	0.4	dB
		f = 10 to 190 MHz	–0.1	–	0.5	dB
		f = 190 to 200 MHz	–0.1	–	0.4	dB
$S_{11}$	input return losses	f = 5 to 200 MHz	20	–	–	dB
$S_{22}$	output return losses	f = 5 to 200 MHz	20	–	–	dB
$S_{21}$	phase response	f = 5 MHz	–45	–	45	dB
$S_{12}$	reverse isolation	f = 5 to 200 MHz	–	–	–42	dB
CTB	composite triple beat	6 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 37 MHz; note 1	–	–	–74	dB
		10 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 67.25 MHz; note 2	–	–	–68	dB
		28 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 199.25 MHz; note 3	–	–	–57	dB
$X_{mod}$	cross modulation	6 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 37 MHz; note 1	–	–	–66	dB
		10 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 25 MHz; note 2	–	–	–57	dB
		28 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 25 MHz; note 3	–	–	–50	dB
CSO	composite second order distortion	6 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 38 MHz; note 1	–	–	–74	dB
		10 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 68.5 MHz; note 2	–	–	–74	dB
		28 chs flat; $V_o = 50\text{ dBmV}$ ; measured at 200.5 MHz; note 3	–	–	–66	dB
$V_o$	output voltage	$d_{im} = -60\text{ dB}$ ; note 4	62	–	–	dBmV
$d_2$	second order distortion	note 5	–	–	–70	dB
NF	noise figure	f = 70 MHz	–	–	5.3	dB
		f = 200 MHz	–	–	5.5	dB
$I_{tot}$	total current consumption	note 6	145	160	175	mA

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**Notes**

1. From the following frequencies: 7.00, 13.00, 19.00, 25.00, 31.00 and 37.00 MHz.
2. From the following frequencies: 7.00, 13.00, 19.00, 25.00, 31.00, 37.00, 43.00, 55.25, 61.25 and 67.25 MHz.
3. From the following frequencies: 7.00, 13.00, 19.00, 25.00, 31.00, 37.00, 43.00, 55.25, 61.25, 67.25, 77.25, 83.25, 109.25, 115.25, 121.25, 127.25, 133.25, 139.25, 145.25, 151.25, 157.25, 163.25, 169.25, 175.25, 181.25, 187.25, 193.25 and 199.25 MHz.
4. Measured according to DIN45004B:  
 $f_p = 197.25$  MHz;  $V_p = V_o$ ;  
 $f_q = 204.25$  MHz;  $V_q = V_o - 6$  dB;  
 $f_r = 206.25$  MHz;  $V_r = V_o - 6$  dB;  
measured at  $f_p + f_q - f_r = 195.25$  MHz.
5.  $f_p = 83.25$  MHz;  $V_p = 50$  dBmV;  
 $f_q = 115.25$  MHz;  $V_q = 50$  dBmV;  
measured at  $f_p + f_q = 198.5$  MHz.
6. The module normally operates at  $V_B = 24$  V, but is able to withstand supply transients up to  $V_B = 35$  V.

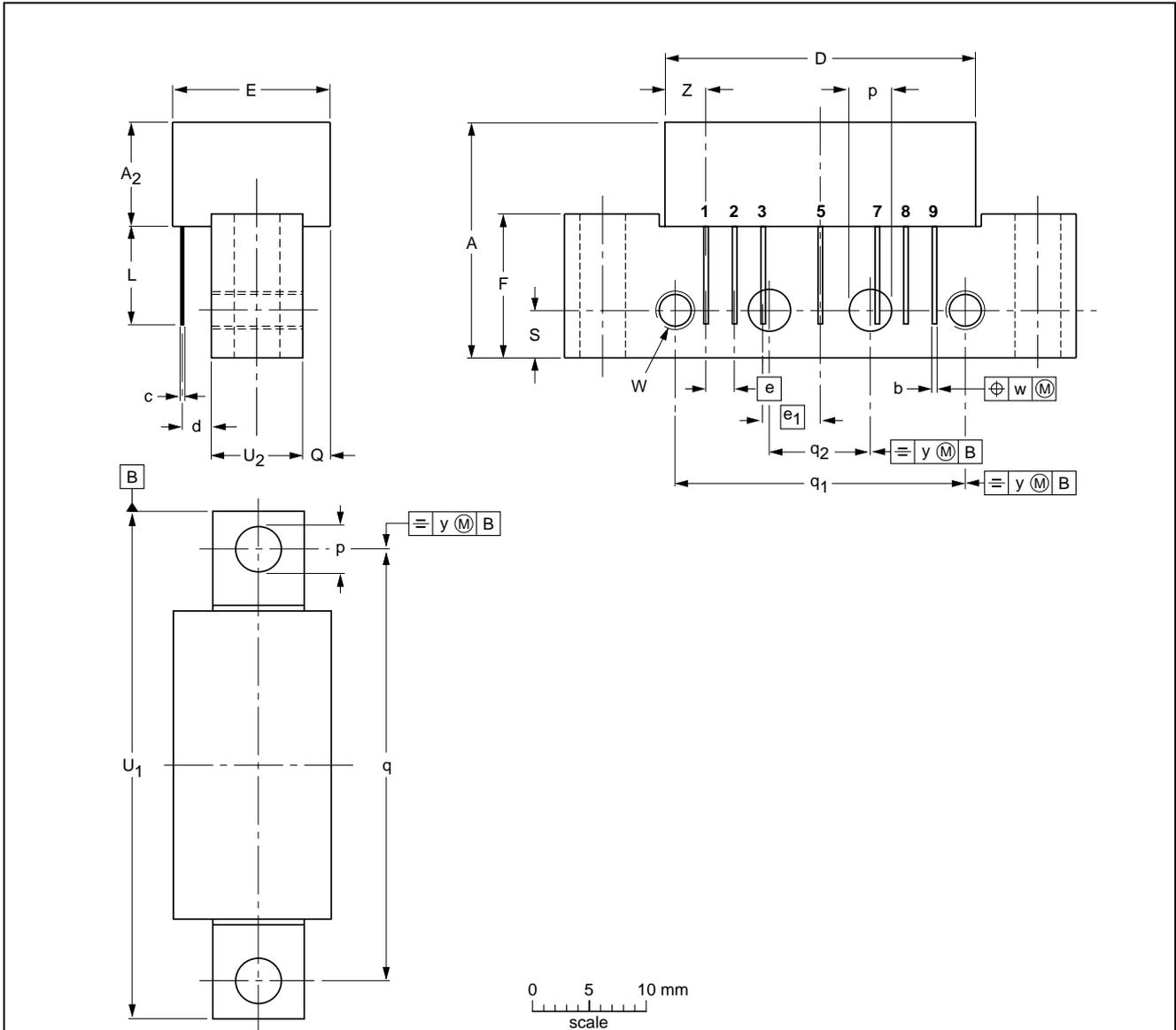
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>2</sub> max.	b	c	D max.	d max.	E max.	e	e <sub>1</sub>	F	L min.	p	Q max.	q	q <sub>1</sub>	q <sub>2</sub>	S	U <sub>1</sub> max.	U <sub>2</sub>	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

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## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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**NOTES**

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